

June 2014

FQA24N50

N-Channel QFET[®] MOSFET 500 V, 24 A, 200 m Ω

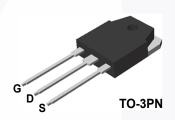
Features

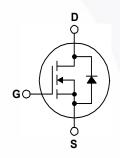
- 24 A, 500 V, $R_{DS(on)}$ = 200 m Ω (Max.) @ V_{GS} = 10 V, I_D = 12 A
- Low Gate Charge (Typ. 90 nC)
- Low Crss (Typ. 55 pF)
- 100% Avalanche Tested
- · RoHS compliant

Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switch mode power supply, power factor correction, electronic lamp ballast based on half bridge.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQA24N50	Unit
V _{DSS}	Drain-Source Voltage		500	V
I _D	Drain Current - Continuous (T _C = 25°C)		24	Α
	- Continuous (T _C = 100°C)		15.2	Α
DM	Drain Current - Pulsed	(Note 1)	96	Α
V_{GSS}	Gate-Source Voltage		± 30	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	1100	mJ
AR	Avalanche Current	(Note 1)	24	Α
E _{AR}	Repetitive Avalanche Energy	(Note 1)	29	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.5	V/ns
P _D	Power Dissipation (T _C = 25°C)		290	W
	- Derate above 25°C		2.33	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C
Γ _L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300	°C

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case		0.43	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink	0.24		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient		40	°C/W

Package Marking and Ordering Information

Parameter

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQA24N50	FQA24N50	TO-3PN	Tube	N/A	N/A	30 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	500			V
ΔBV _{DSS} / ΔΤ _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		0.53		V/°C
I _{DSS}	Zoro Coto Voltago Drain Current	V _{DS} = 500 V, V _{GS} = 0 V			1	μΑ
	Zero Gate Voltage Drain Current	V _{DS} = 400 V, T _C = 125°C			10	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V			-100	nA

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 12 A		0.156	0.2	Ω
9 _{FS}	Forward Transconductance	$V_{DS} = 50 \text{ V}, I_{D} = 12 \text{ A}$		22	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V,	 3500	4500	pF
C _{oss}	Output Capacitance	f = 1.0 MHz	 520	670	pF
C _{rss}	Reverse Transfer Capacitance		 55	70	pF

Switching Characteristics

t _{d(on)}	Turn-On Delay Time	V _{DD} = 250 V, I _D = 24 A,	 80	170	ns
t _r	Turn-On Rise Time	$R_G = 25 \Omega$	 250	500	ns
t _{d(off)}	Turn-Off Delay Time		 200	400	ns
t _f	Turn-Off Fall Time	(Note 4)	 155	320	ns
Q_g	Total Gate Charge	V _{DS} = 400 V, I _D = 24 A,	 90	120	nC
Q_{gs}	Gate-Source Charge	V _{GS} = 10 V	 23		nC
Q_{gd}	Gate-Drain Charge	(Note 4)	 44		nC

Drain-Source Diode Characteristics and Maximum Ratings

		9				
Is	Maximum Continuous Drain-Source Diode Forward Current				24	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forw			96	Α	
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 24 A			1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 24 A,		400		ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/μs		4.3		μС

Notes

 $^{{\}bf 1.} \ {\bf Repetitive} \ {\bf rating: pulse \ width \ limited \ by \ maximum \ junction \ temperature.}$

^{2.} L = 3.4 mH, I_{AS} = 24 A, V_{DD} = 50 V, R_{G} = 25 Ω , starting T_{J} = 25°C.

^{3.} I $_{SD} \leq$ 24 A, di/dt \leq 200 A/µs, V $_{DD} \leq$ BV $_{DSS,}$ starting $\,$ T $_{J}$ = 25°C.

^{4.} Essentially independent of operating temperature.

Typical Characteristics

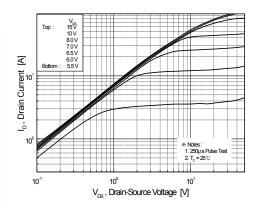


Figure 1. On-Region Characteristics

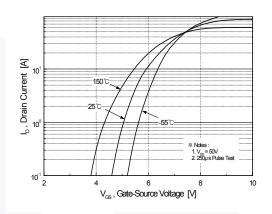


Figure 2. Transfer Characteristics

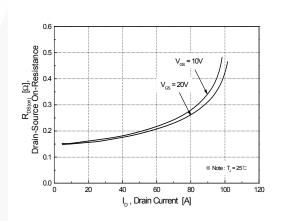


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

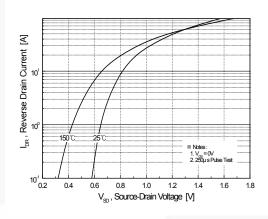


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

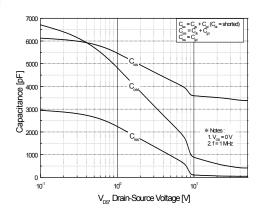


Figure 5. Capacitance Characteristics

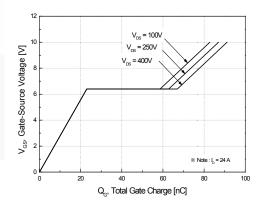


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

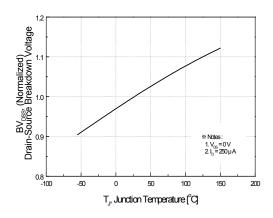
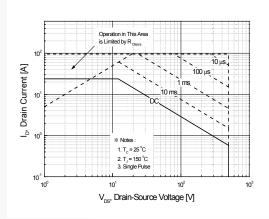


Figure 7. Breakdown Voltage Variation vs. Temperature





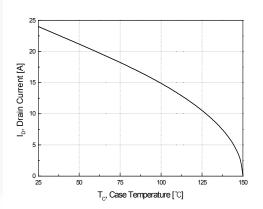


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

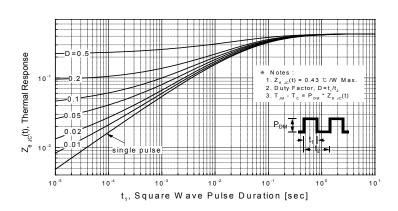


Figure 11. Transient Thermal Response Curve

Figure 12. Gate Charge Test Circuit & Waveform

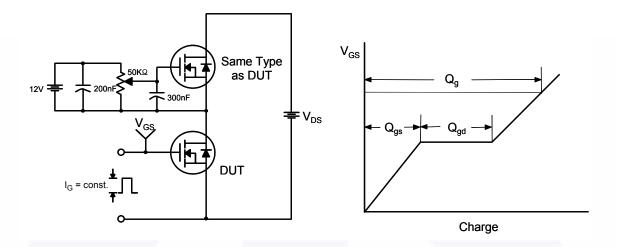


Figure 13. Resistive Switching Test Circuit & Waveforms

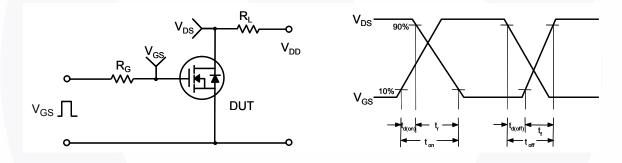
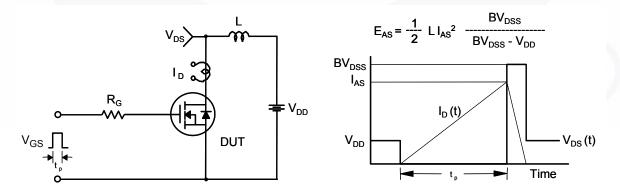


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



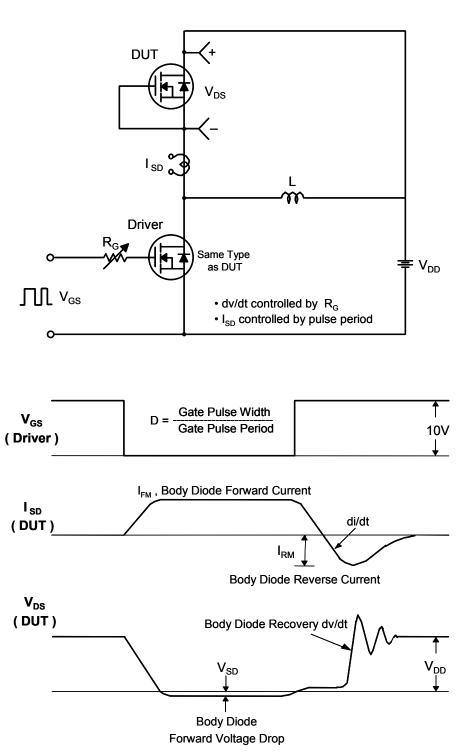


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

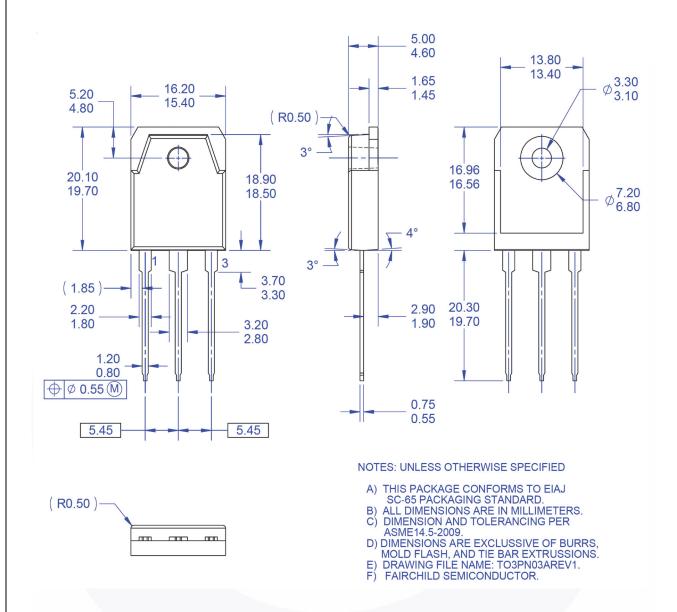


Figure 16. TO3PN, 3-Lead, Plastic, EIAJ SC-65

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